



INTERNATIONAL ATOMIC ENERGY AGENCY
UNITED NATIONS EDUCATIONAL, SCIENTIFIC AND CULTURAL ORGANIZATION



INTERNATIONAL CENTRE FOR THEORETICAL PHYSICS
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SMR/382-20

WORKSHOP ON SPACE PHYSICS:
"Materials in Microgravity"
27 February - 17 March 1989

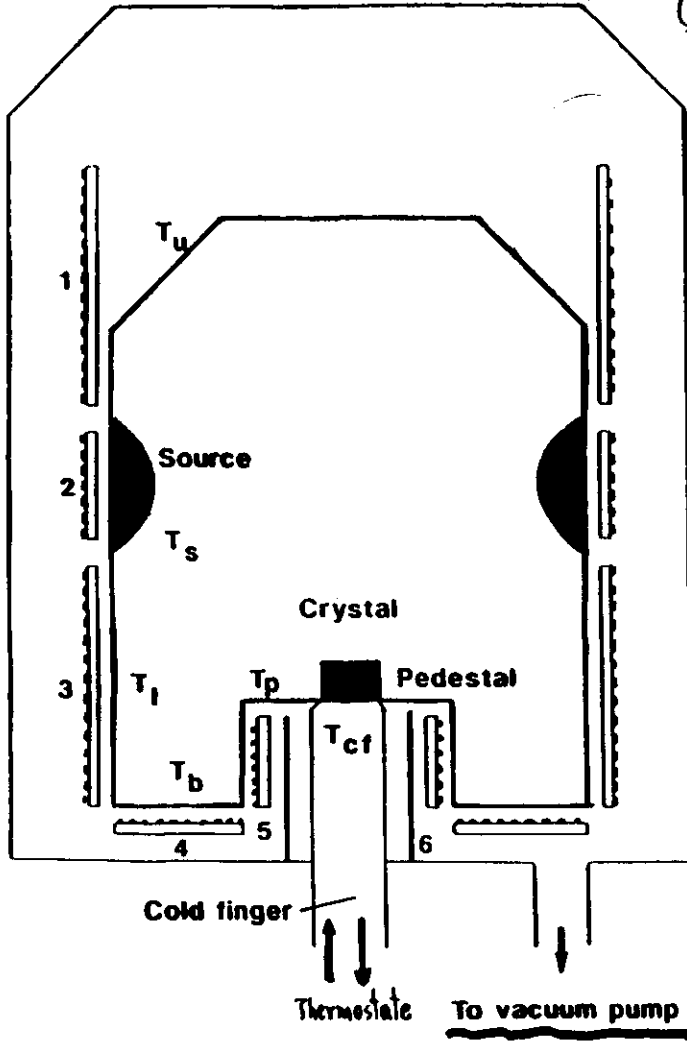
"Growth Rate: Ground Based"

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ETH
Zurich, Switzerland

Please note: These are preliminary notes intended for internal distribution only.

VAPOUR GROWTH TRANSPARENT FURNACE

(SCHEMATIC)



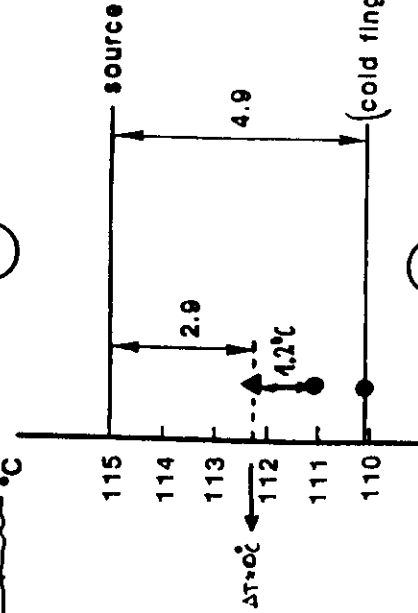
- | | |
|-----------------|--------------------|
| 1 Upper heater | 4 Bottom heater |
| 2 Source heater | 5 Pedestal heater |
| 3 Lower heater | 6 Radiation shield |

Fig.17

- $T \pm 0.1^\circ\text{C}$ (H₁₀₀)
- $T_{cr} \pm 0.02^\circ\text{C}$
- Vacuum Isolation
- Thermostated Cooling Finger } CF

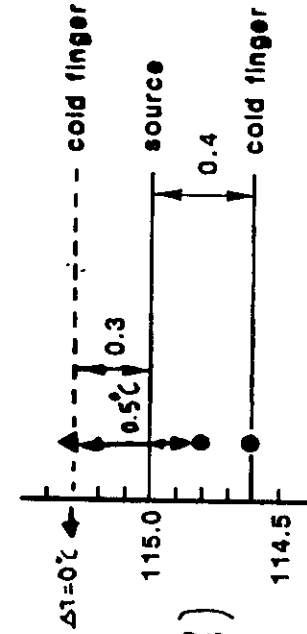
high T experiment

(A)



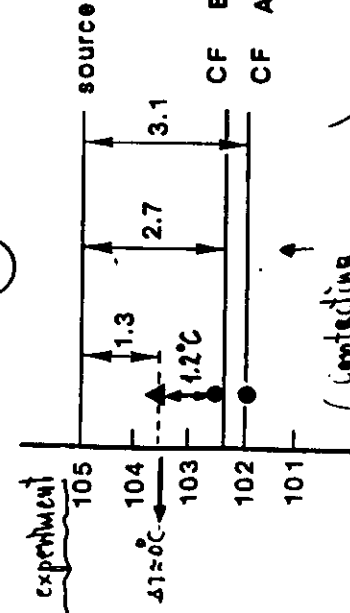
high T experiment

(B)



low T experiment

(A)



(Contacting difficulties of the cold finger)

- Onset of EVAPORATION ($\Delta T = 0.0 \pm 0.1^\circ\text{C}$)
- GROWTH
- NUCLEATION

Problems of the cold finger contact overcome via internal calibration of undercooling at $\Delta T = 0^\circ\text{C} \pm 0.1$

EQUILIBRIUM: $\rho_{u,T}(\text{source surface}) = \rho_{c,T}(\text{crystal surface})$

Fig.21

TEMPERATURE MAPPING INSIDE THE AMPOULE.

Rotating T-sensor System
introduces some slight errors

Drawback

Advantages:

- 1) T-mapping
First panoramic view inside the ampoule.
- 2) Rather easy to perform.

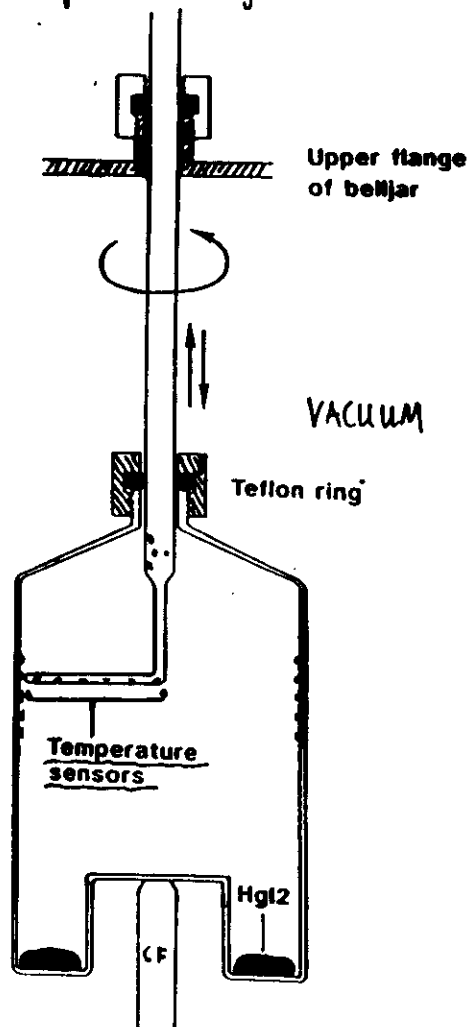
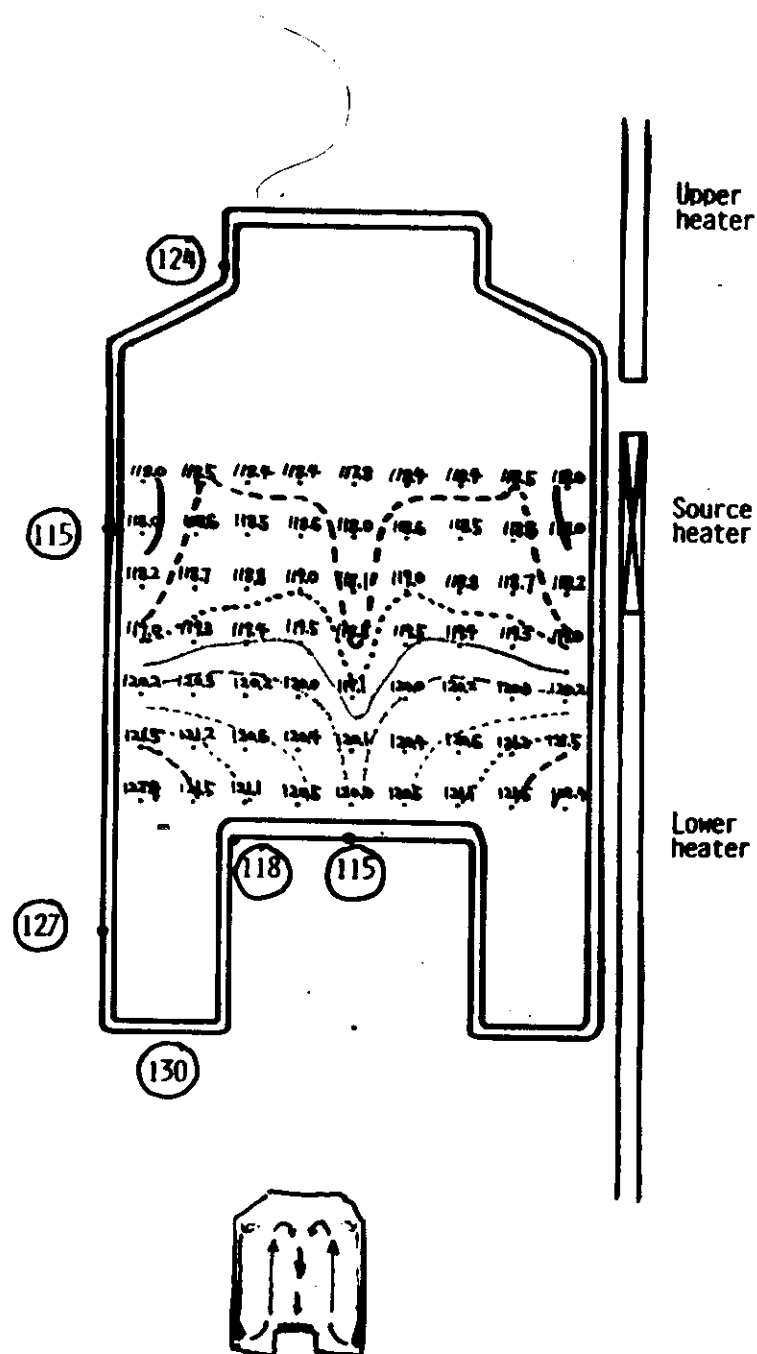
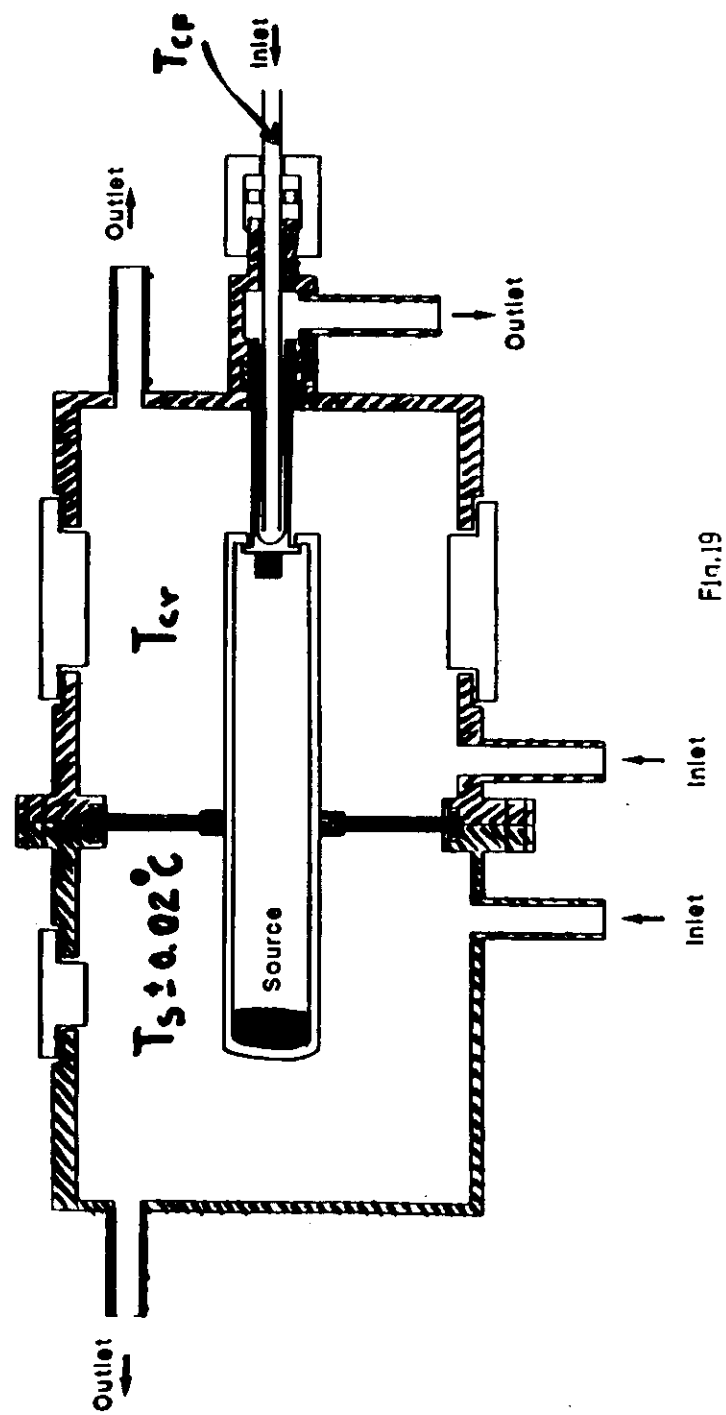
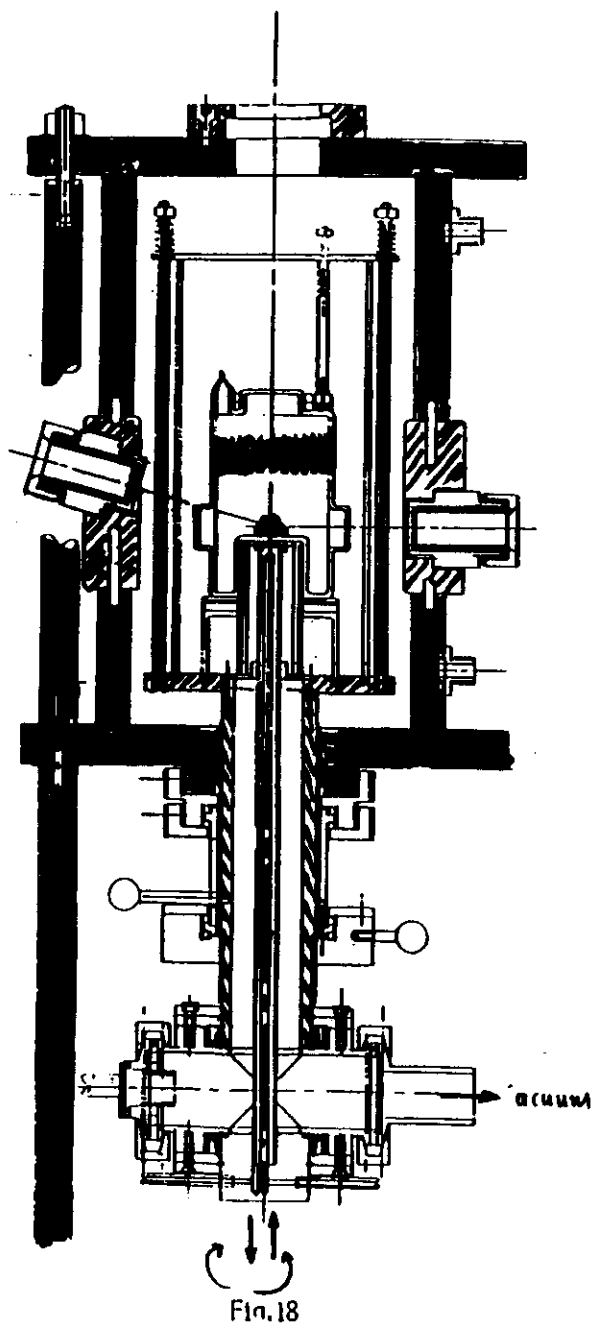


Fig.20

IN α -HgI₂ ATMOSPHERE





Growth rate vs time

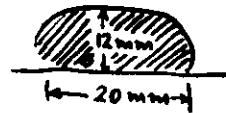
DECREASING

1. α -HgI₂ Kobayashi et al 1983
Cadoret et al

2. Hg₂Cl₂ Singh et al 1987

This work : long term experiment (1100 hrs).

lateral + vertical } crystal size
photographically
measured.



- Growth rate stops after ≈ 60 hrs
- Growth curve saturation $\rightarrow$ Surface macroscopically rough (irregular multifaceting).

- Growth can continue after increase of undercooling.
- Partial evaporation $\rightarrow$ reproducible growth curve

No surface cleaning
effect to move
growth step.

GROWTH $\rightarrow$ SIZE DEPENDENT

THERMAL CONDUCTION
PROBLEM? (Anisotropy due to layer structure)

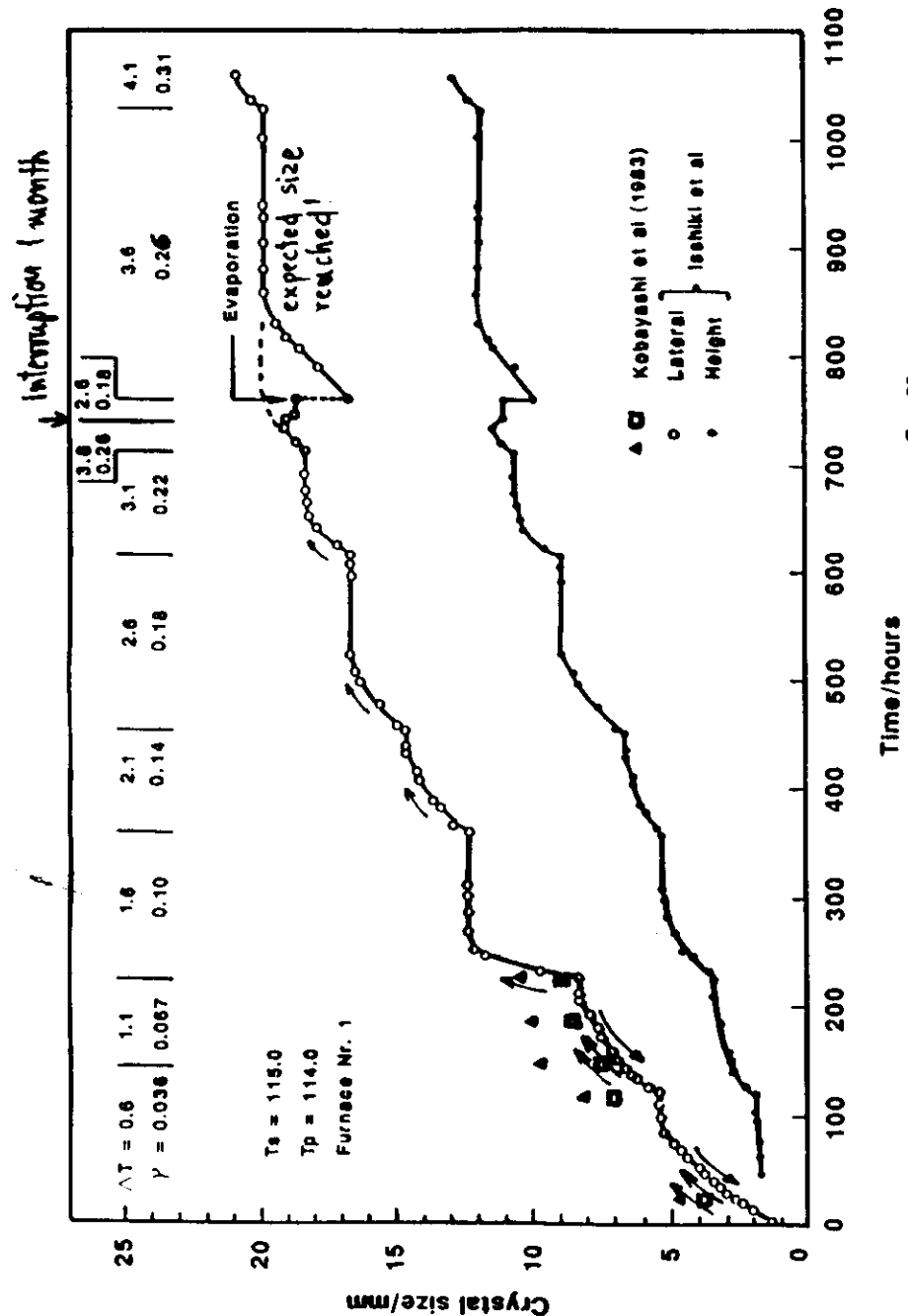


Fig. 22

thermal conductivity α -MgI₂

(De Groer et al., J. Phys. Chem. Solids 43 (1982) 341)

$T = 300\text{K}$ $\parallel$ c-axis 0.4 W/mK

$\perp$ c-axis 2.0 W/mK

Assumption of calculation: crystal surface temperature,
also supersaturation,
depends on heat dissipation
rate $\rightarrow$ crystal size

- crystal habit $\rightarrow$ cube
c-axis $\perp$ pedestal
- growth rate vs supersaturation - parabolic.
- heat of condensation dissipated via the
crystal-pedestal contact.

- Fitting to the first exp. point

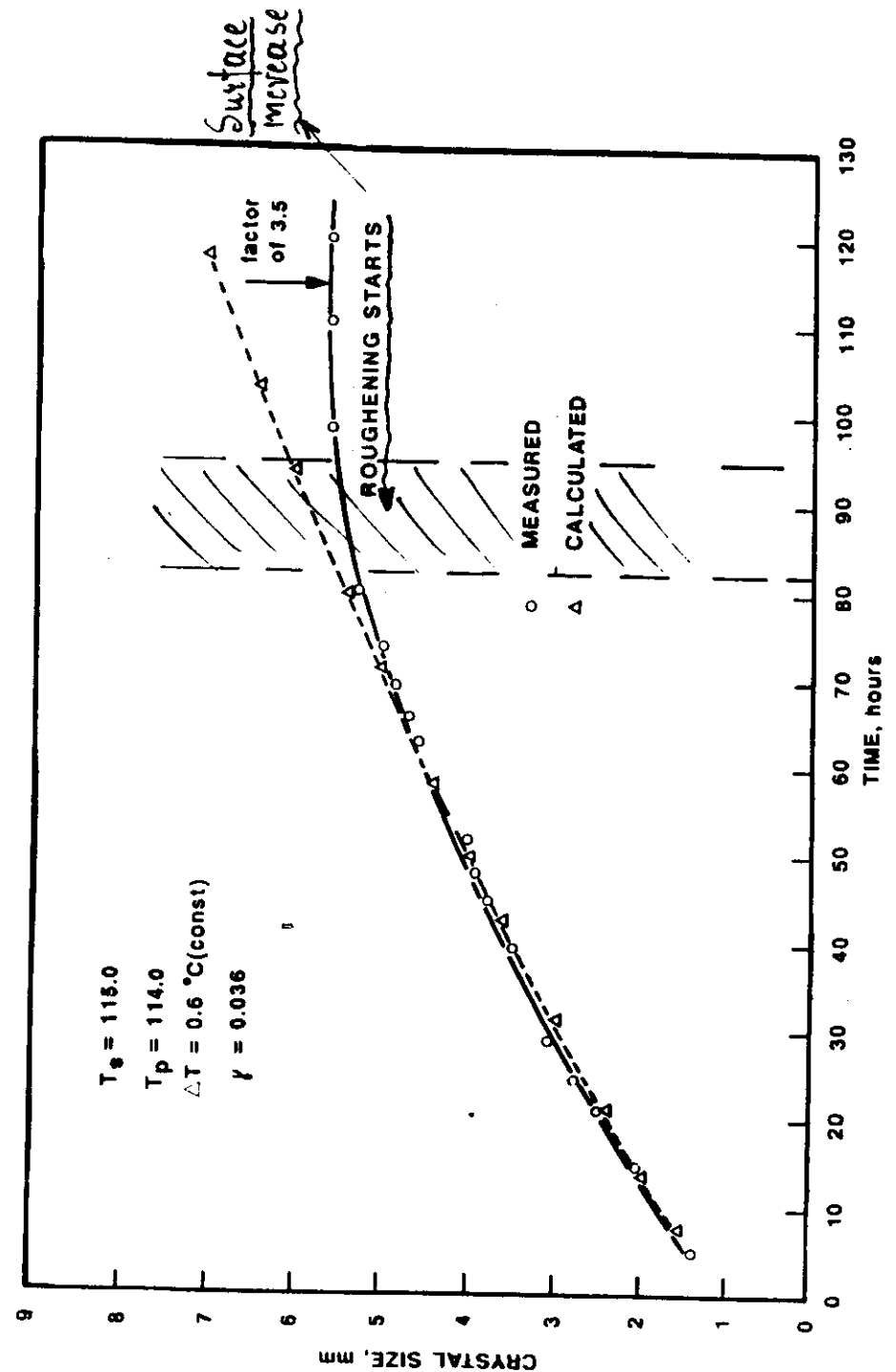
good agreement calculation $\leftrightarrow$ experiment till
the roughening stage.

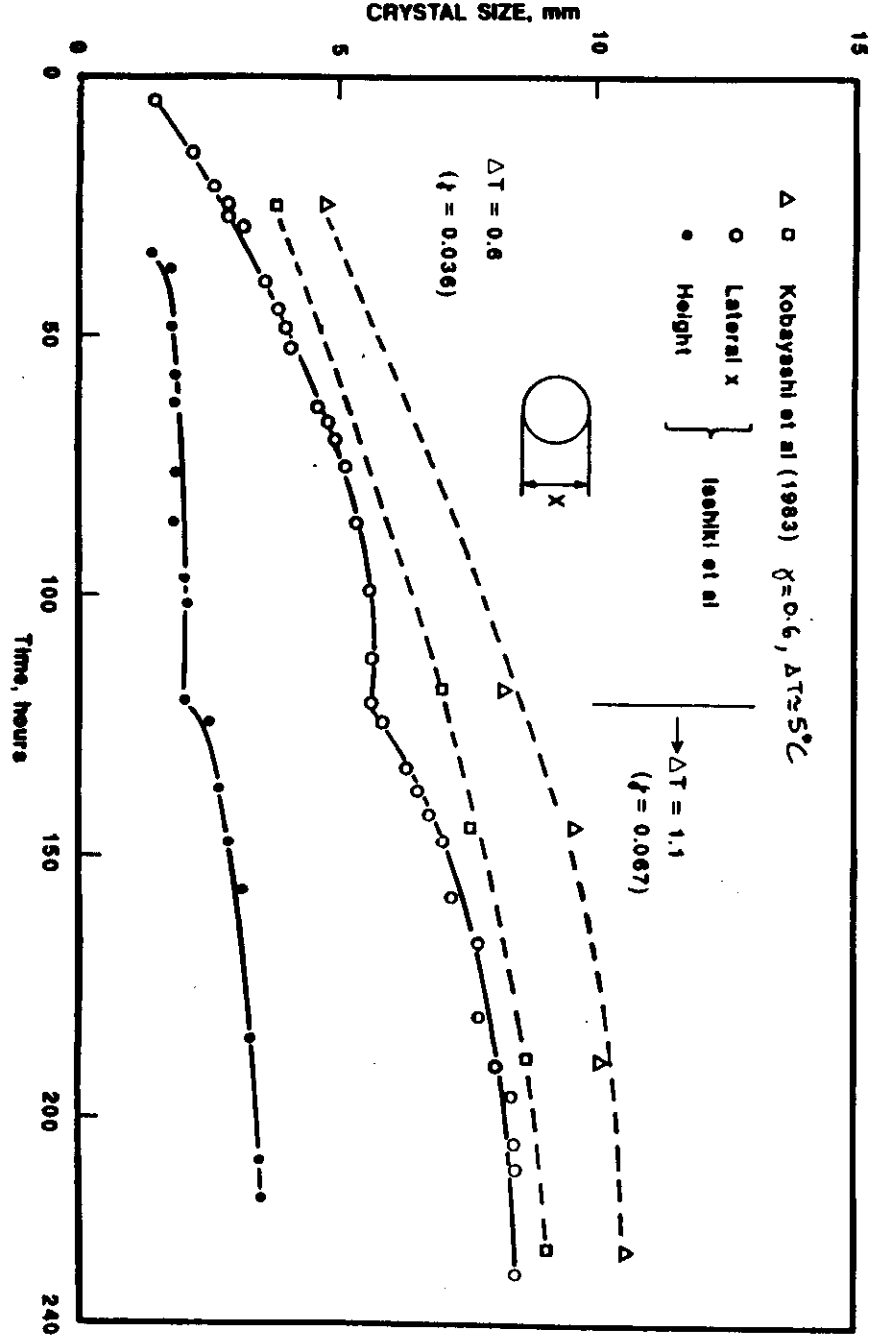
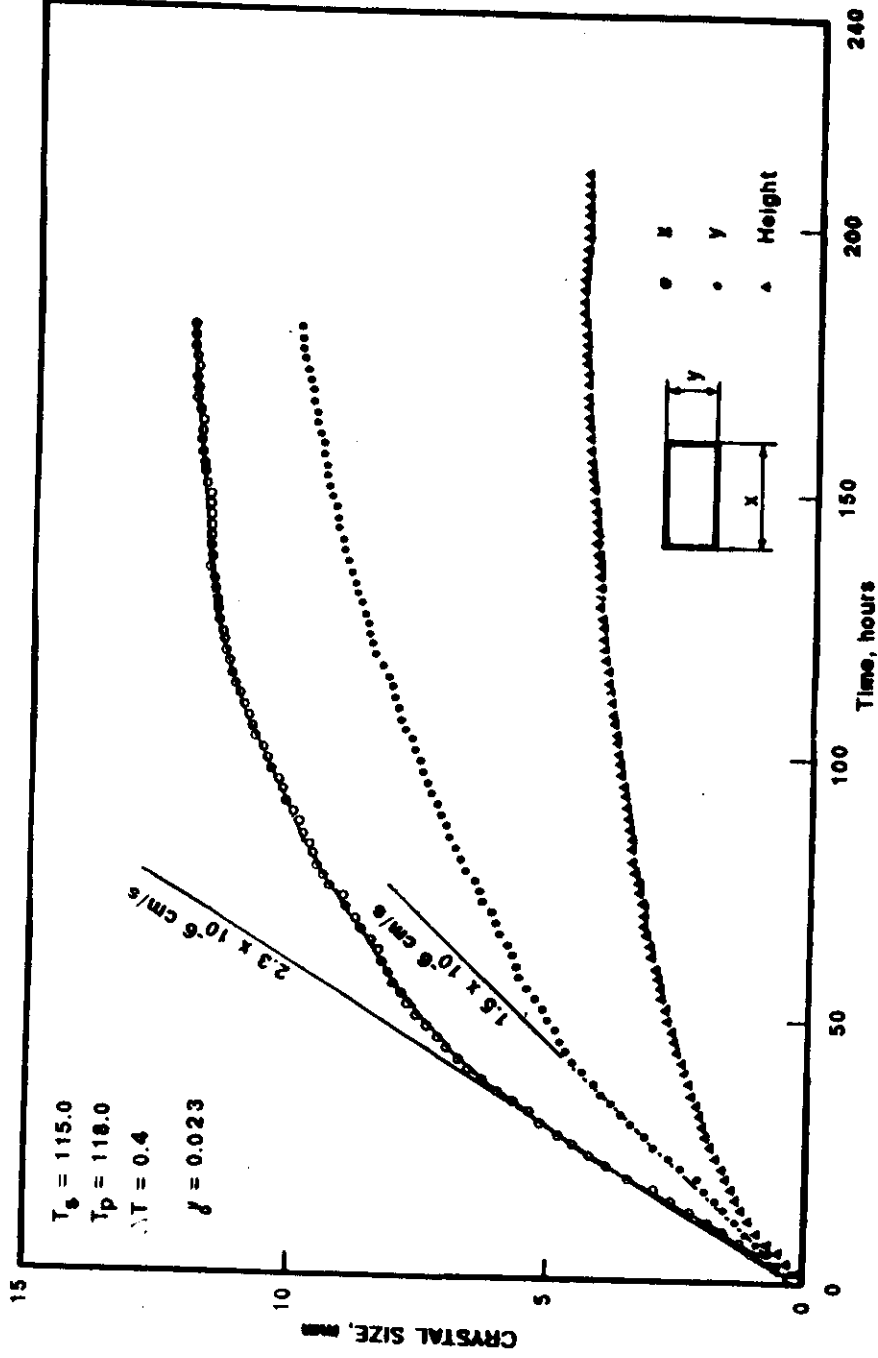
Roughening (microfaceting) $\rightarrow$ Change from kinetically
increases the condensation surface + heat of condensation
stabilised to equilibrium faces?

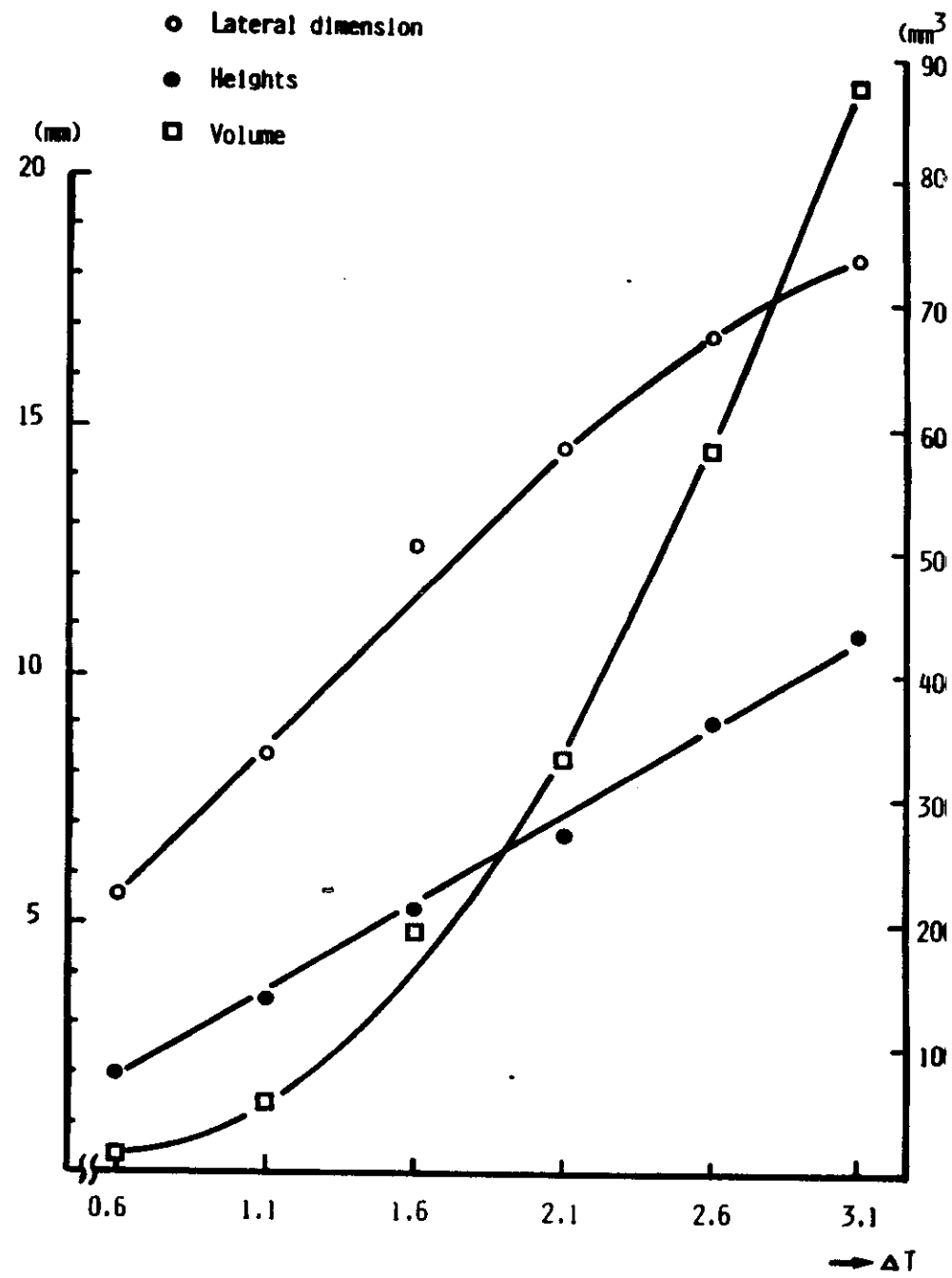
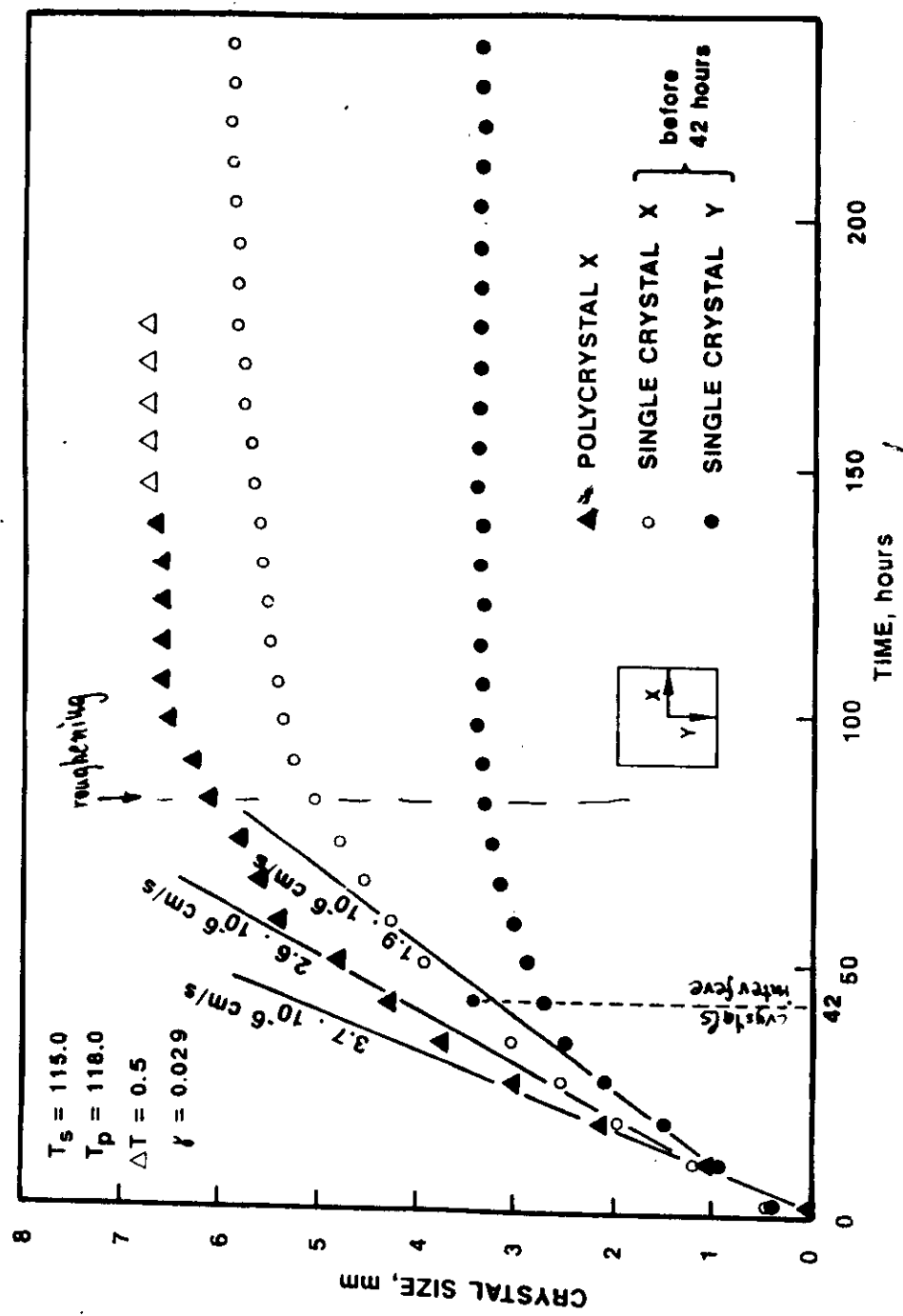
Factor 3.5 $\rightarrow$ Agreement calculation $\rightarrow$ experiment

After $\Delta T_{\text{surf}} = 0$, why no relaxation and then growth?

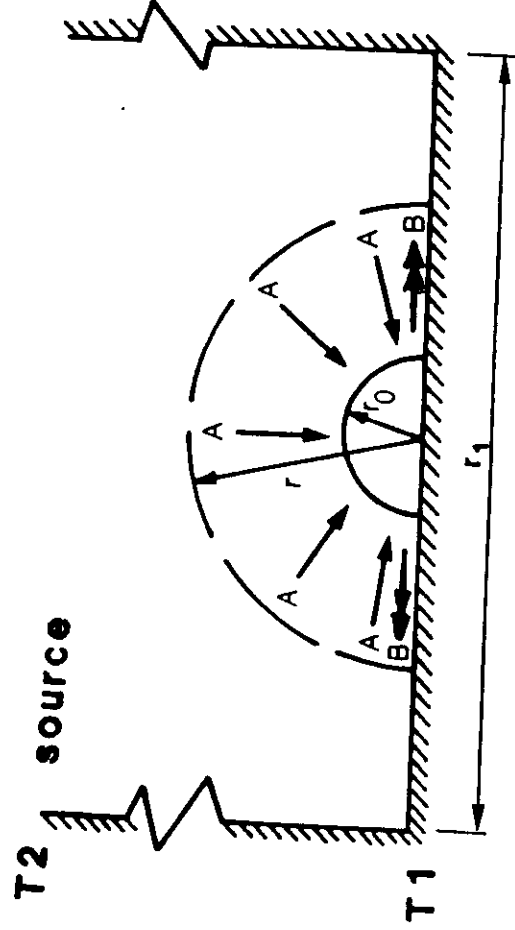
Possibly because gas heat dissipation continuous.



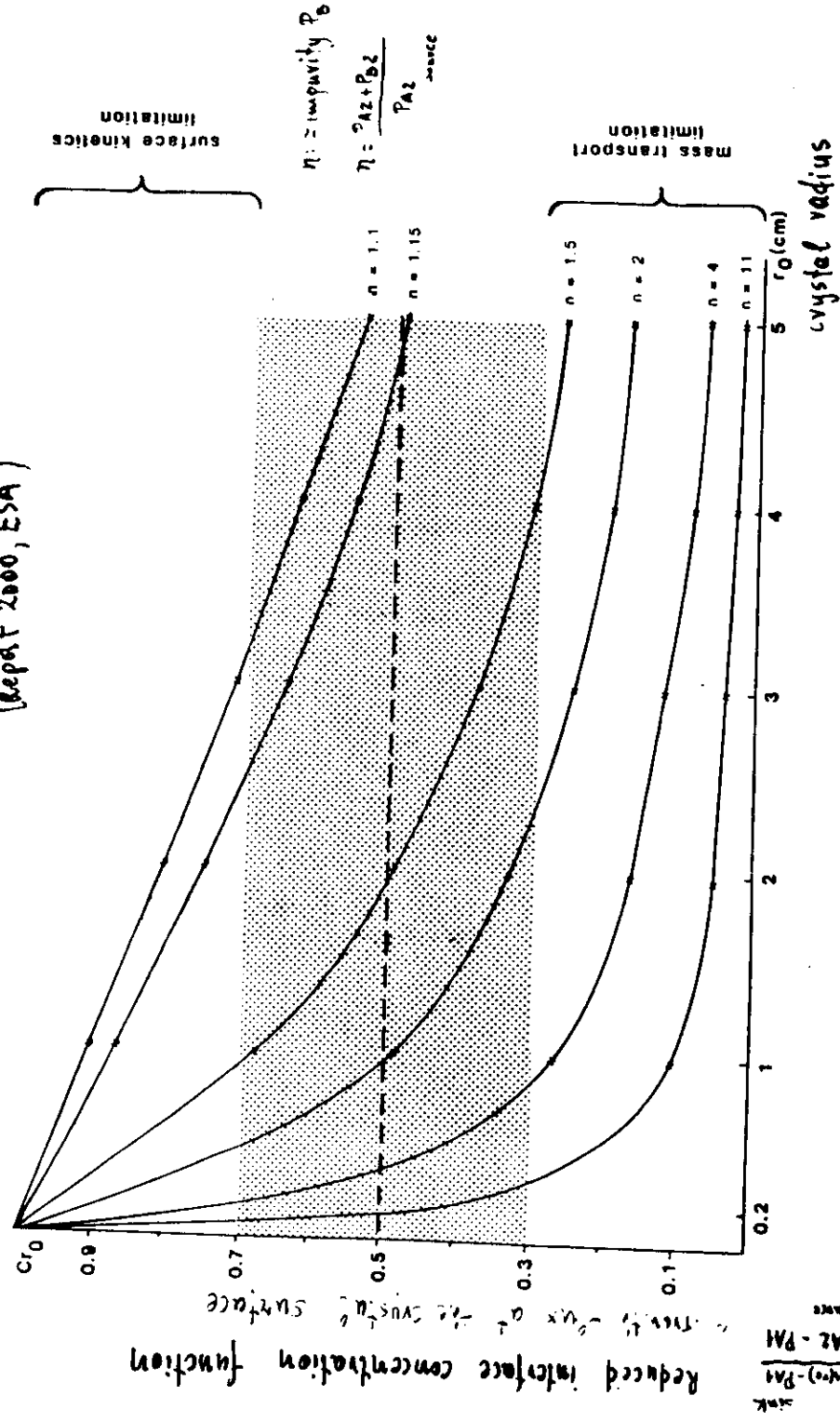




After Cadoret (ESA Report 2000)



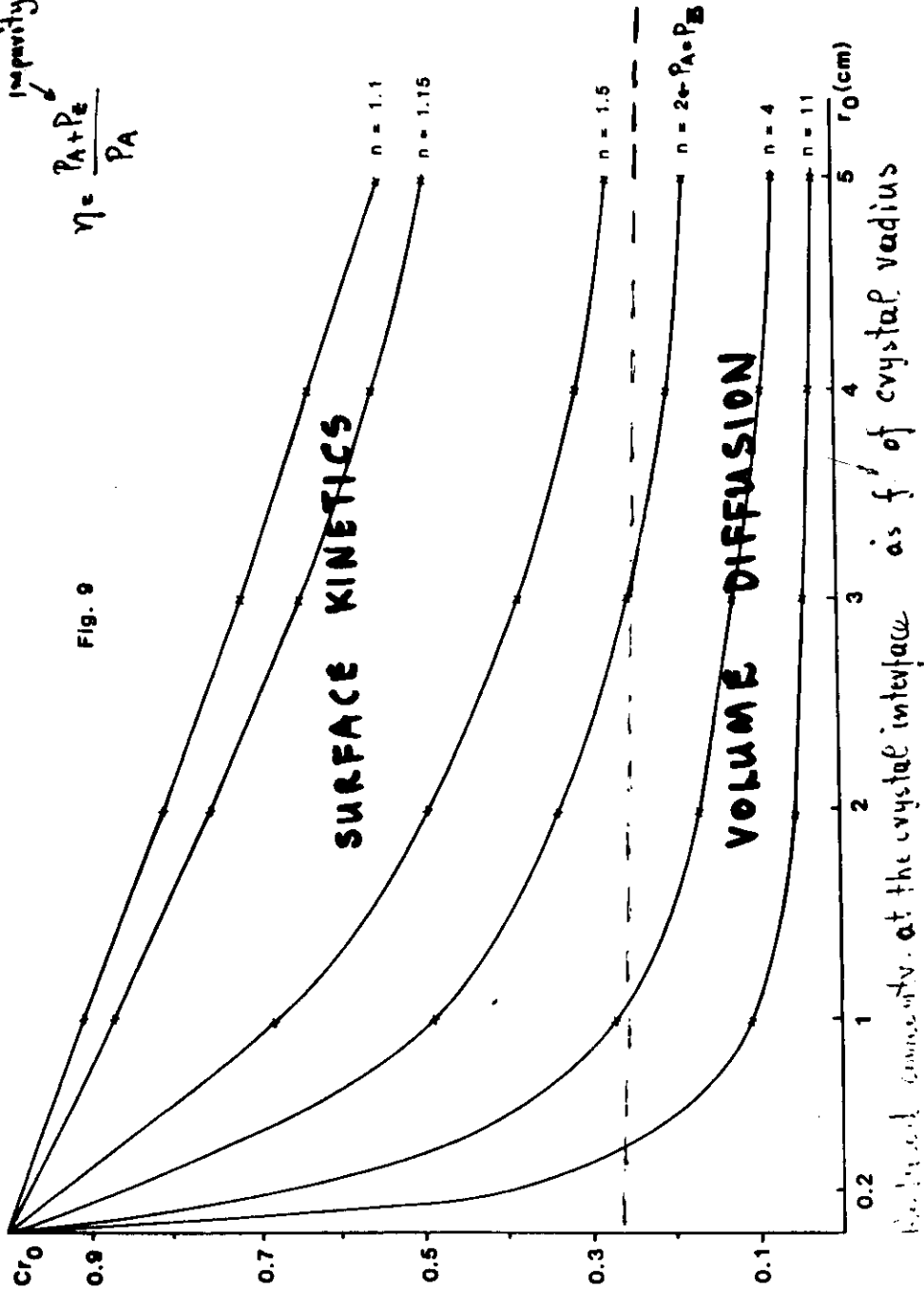
R. Cadoret
(Repat 2000, ESA)



R. Cadoret 1980

$$\eta = \frac{P_A + P_E}{P_A} \quad \text{impurity}$$

Fig. 9



Pressure gradient of the α -HgI₂ molecules due to the presence of impurities.

$$\frac{\Delta P}{\Delta(r-r_0)} \times 10^5 \text{ atm cm}^{-1}$$

near the crystal

$$r - r_0 = 0.2 \text{ cm}$$

R. CADORET
(Report 2000, ESA)

$$r - r_0 = 2 \text{ cm}$$

far from the crystal

$$r - r_0 = 5 \text{ cm}$$

distance from the interface (crystal-v)

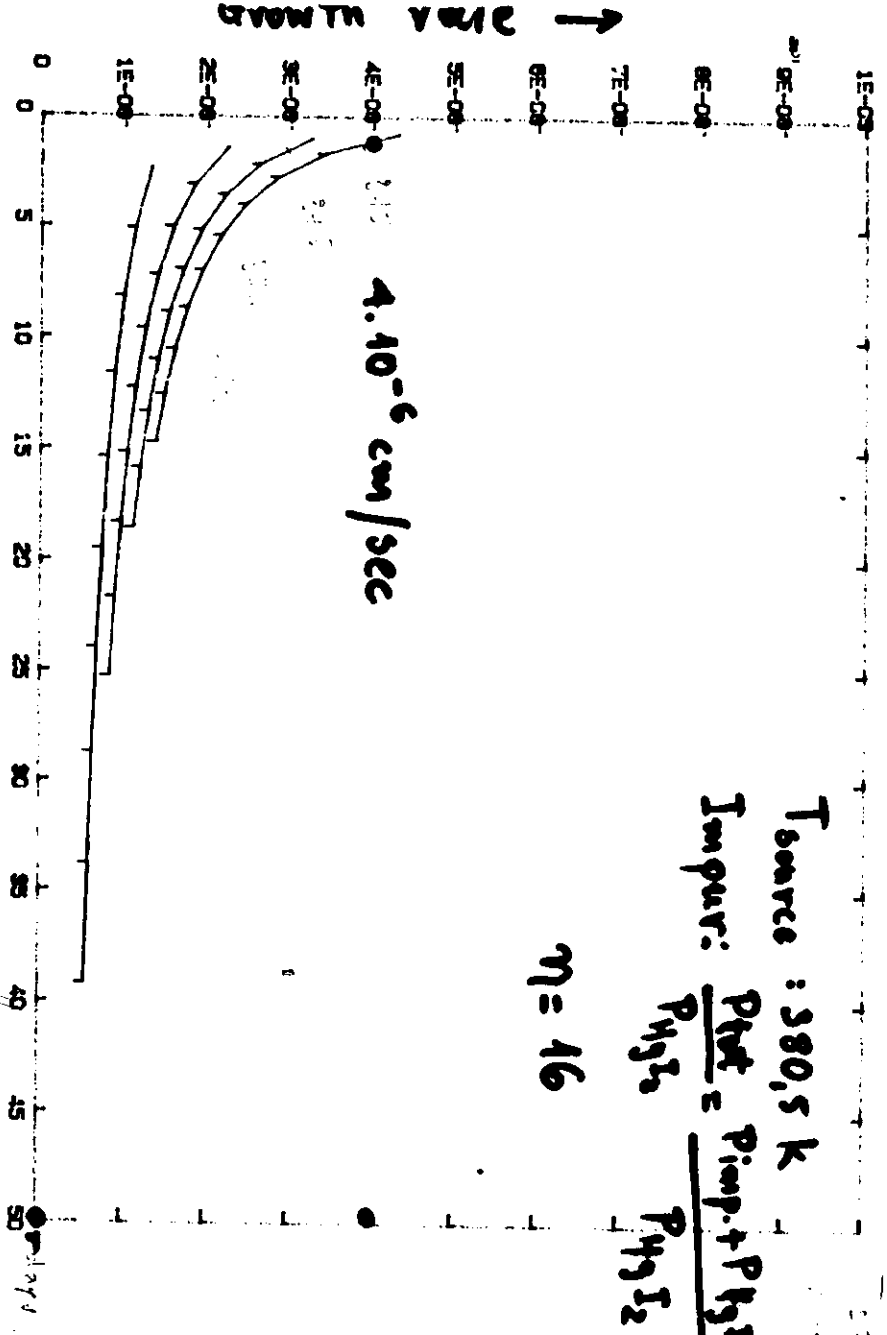
→ increasing impurities concentration

R. Cadoret (1987)

82

$T_{\text{source}} : 380,5 \text{ K}$
 $T_{\text{impur}} : \frac{P_{\text{tot}}}{P_{\text{H}_2\text{I}_2}} = \frac{P_{\text{imp}} + P_{\text{H}_2\text{I}_2}}{P_{\text{H}_2\text{I}_2}} = \eta$

$\eta = 16$



time [days]

R. Cadoret (1987)

$\eta = 64$

